

High Voltage Thyristor Module

$$V_{RRM} = 2200\text{ V}$$

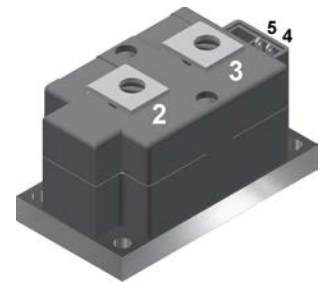
$$I_{TAV} = 600\text{ A}$$

$$V_T = 1,06\text{ V}$$

Single Thyristor

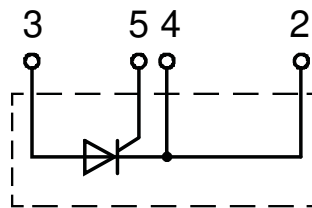
Part number

MCO600-22io1



Backside: isolated

 E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al₂O₃-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: Y1

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Disclaimer Notice

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.



Thyristor			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			2300	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			2200	V
I_{RD}	reverse current, drain current	$V_{R/D} = 2200 V$	$T_{VJ} = 25^{\circ}C$		2	mA
		$V_{R/D} = 2200 V$	$T_{VJ} = 125^{\circ}C$		40	mA
V_T	forward voltage drop	$I_T = 600 A$	$T_{VJ} = 25^{\circ}C$		1,12	V
		$I_T = 1200 A$			1,34	V
		$I_T = 600 A$	$T_{VJ} = 125^{\circ}C$		1,06	V
		$I_T = 1200 A$			1,33	V
I_{TAV}	average forward current	$T_C = 85^{\circ}C$	$T_{VJ} = 140^{\circ}C$		600	A
$I_{T(RMS)}$	RMS forward current	180° sine			940	A
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 140^{\circ}C$		0,81	V
r_T	slope resistance				0,4	mΩ
R_{thJC}	thermal resistance junction to case				0,065	K/W
R_{thCH}	thermal resistance case to heatsink			0,02		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		1770	W
I_{TSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		15,0	kA
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		16,2	kA
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 140^{\circ}C$		12,8	kA
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		13,8	kA
I^2t	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		1,13	MA ² s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		1,09	MA ² s
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 140^{\circ}C$		812,8	kA ² s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		788,8	kA ² s
C_J	junction capacitance	$V_R = 700V \quad f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		469	pF
P_{GM}	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 140^{\circ}C$		120	W
		$t_p = 300 \mu s$			60	W
P_{GAV}	average gate power dissipation				20	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 140^{\circ}C; f = 50 \text{ Hz}$ repetitive, $I_T = 1800 A$			100	A/μs
		$t_p = 200 \mu s; di_G/dt = 1 A/\mu s;$ $I_G = 1 A; V_D = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 600 A$			500	A/μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V_D = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty; \text{ method 1 (linear voltage rise)}$	$T_{VJ} = 140^{\circ}C$		1000	V/μs
V_{GT}	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		2	V
			$T_{VJ} = -40^{\circ}C$		3	V
I_{GT}	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		300	mA
			$T_{VJ} = -40^{\circ}C$		400	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^{\circ}C$		0,25	V
I_{GD}	gate non-trigger current				10	mA
I_L	latching current	$t_p = 30 \mu s$	$T_{VJ} = 25^{\circ}C$		400	mA
		$I_G = 1 A; di_G/dt = 1 A/\mu s$				
I_H	holding current	$V_D = 6 V \quad R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$		300	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}C$		2	μs
		$I_G = 1 A; di_G/dt = 1 A/\mu s$				
t_q	turn-off time	$V_R = 100 V; I_T = 600 A; V_D = \frac{2}{3} V_{DRM}$ $di/dt = 10 A/\mu s; dv/dt = 50 V/\mu s; t_p = 200 \mu s$	$T_{VJ} = 125^{\circ}C$		350	μs



Package Y1			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			600	A
T_{VJ}	virtual junction temperature		-40		140	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight				650		g
M_D	mounting torque		4,5		7	Nm
M_T	terminal torque		11		13	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	16,0			mm
$d_{Spb/Apb}$		terminal to backside	25,0			mm
V_{ISOL}	isolation voltage	t = 1 second	4800			V
		t = 1 minute	4000			V



Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.# (33-36)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCO600-22io1	MCO600-22io1	Box	2	474339

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 140^{\circ}C$



Thyristor

$V_{0\ max}$	threshold voltage	0,81	V
$R_{0\ max}$	slope resistance *	0,22	mΩ

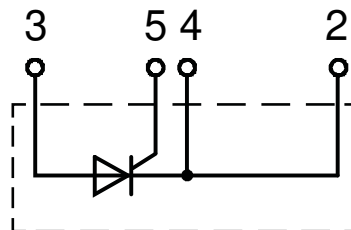


Outlines Y1



Optional accessories for modules

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red
 Type ZY 180L (L = Left for pin pair 4/5) UL 758, style 3751



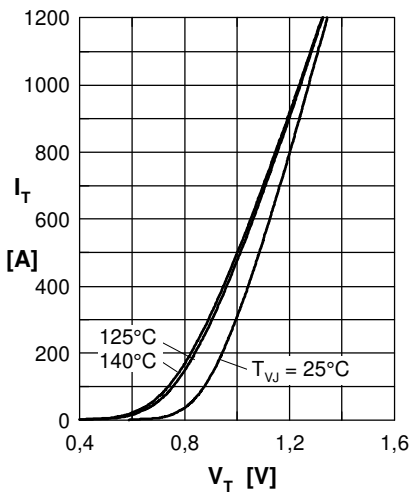
Thyristor


Fig. 1 Forward characteristics

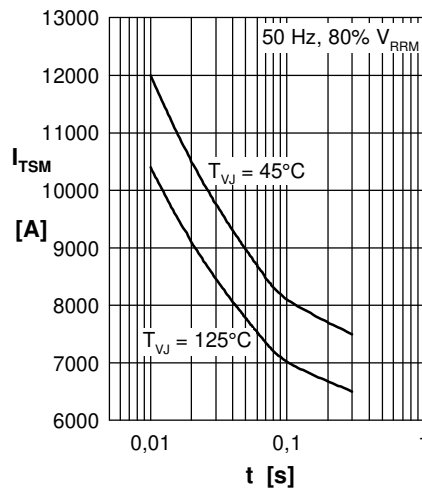


Fig. 2 Surge overload current

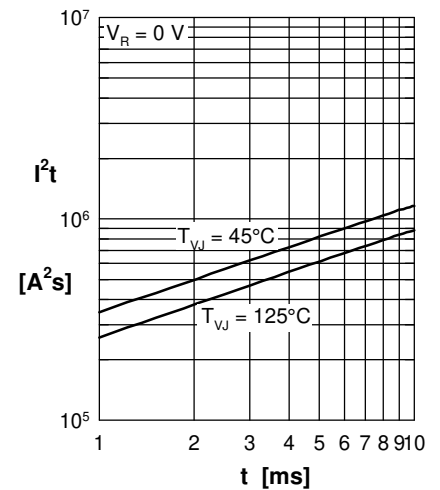
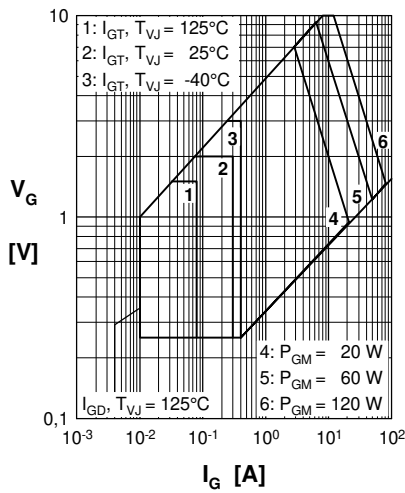

 Fig. 3 I^2t versus time (1-10 ms)


Fig. 4 Gate trigger characteristics

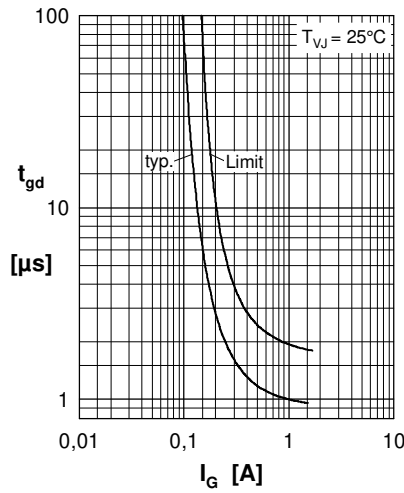


Fig. 5 Gate controlled delay time

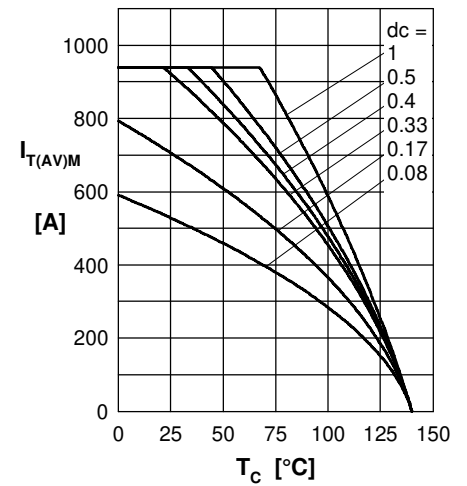


Fig. 6 Max. forward current at case temperature

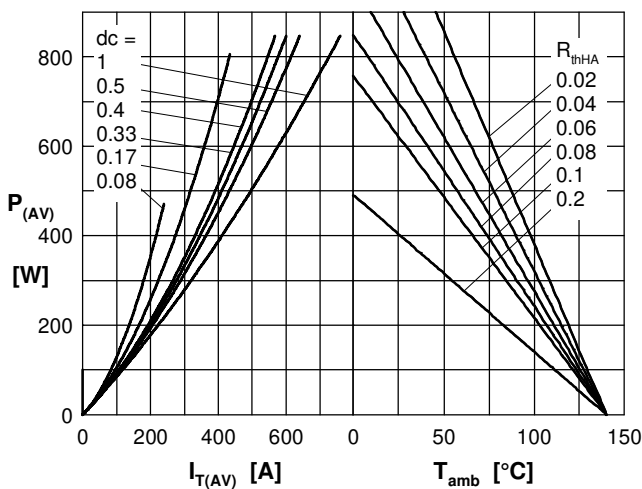
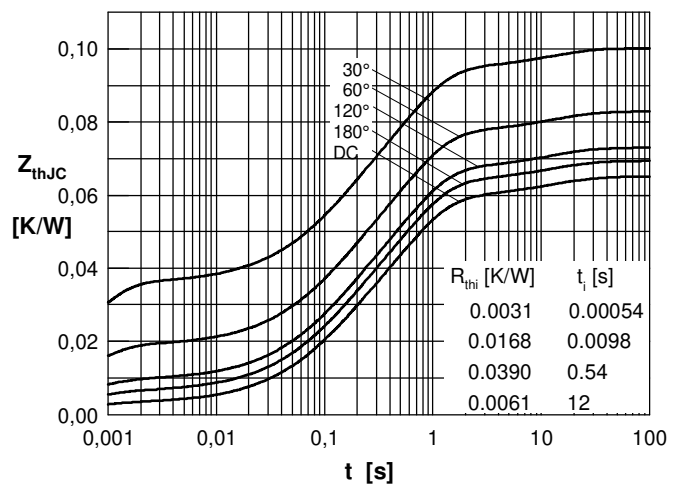

 Fig. 7a Power dissipation versus direct output current
 Fig. 7b and ambient temperature


Fig. 8 Transient thermal impedance